

Abstracts

High Performance Monolithic Power Amplifier Using a Unique Ion Implantation Process (1986 [MCS])

S.K. Wang, K.G. Wang and C.D. Chang. "High Performance Monolithic Power Amplifier Using a Unique Ion Implantation Process (1986 [MCS])." 1986 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 86.1 (1986 [MCS]): 5-7.

State-of-the-art X-band power FETs and monolithic amplifiers have been fabricated by a high yield planar process using a unique double-peaked implant profile. A 1-mm FET has achieved 40 percent power added efficiency with 720 mW output power and 6.3 dB gain at 10 GHz. A two-stage monolithic amplifier has delivered 2.2 W output power at 9.5 GHz for a record 0.6 W/mm power density. The monolithic amplifier chips have also achieved 20 percent dc-yield and 5 percent uniformity in I_{DSS} and V_{PO} .

[Return to main document.](#)